

## Current Transducer HAIS 50 .. 400-P HAIS 50 .. 150-TP

For the electronic measurement of currents: DC, AC, pulsed..., with galvanic separation between the primary circuit and the secondary circuit.









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All data	are	given	with	$R_{\scriptscriptstyle L}$	=	10	kΩ

#### **Electrical data** Primary nominal Primary current Type rms current $I_{PN}(A)$ measuring range $I_{PM}(A)$ ±150 HAIS 50-P/50-TP 1) 100 ±300 HAIS 100-P/100-TP 1) 150 ±450 HAIS 150-P/150-TP 1) 200 ±600 **HAIS 200-P** 400 ±600 **HAIS 400-P** $\overline{G}_{\mathrm{Th}}$ Theorical sensitivity @ $I_{\tiny \mathrm{DN}}$ 0.625 Analog output voltage @ $I_{\scriptscriptstyle D}$ $V_{\rm OE}$ +(0.625· $I_{\rm P}$ / $I_{\rm PN}$ ) V $V_{\rm out}$ Reference voltage 2) $V_{ref}$ Output voltage 2.5 ±0.025 Output impedance typ. 200 Ω Load impedance ≥200 kΩ Load resistance ≥2 kΩ Output internal resistance <5 0 Capacitive loading (±20 %) 4.7 nF Supply voltage (±5 %) 3) 5 V Current consumption @ $U_c = 5 \text{ V}$ <19 mΑ

Accuracy - Dynamic performance data	Accuracy -	Dynamic	performance	data
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X	Accuracy 4) @ $I_{PN}$ , $T_A = 25^{\circ}$ C		≤± 1	$\%$ of $I_{_{PN}}$
$\varepsilon_{_{\scriptscriptstyle L}}$	Linearity error 0 $I_{\scriptscriptstyle{\mathrm{PM}}}$		≤±0.5	% of $I_{\scriptscriptstyle{PN}}$
TCV <sub>OE</sub>	Temperature coefficient of $V_{OE}$		≤±0.3	mV/K
$TCV_{ref}$	Temperature coefficient of $V_{ref}$	(+25 +85 °C)	≤±0.01	%/K
		(-40 +25 °C)	≤±0.015	%/K
TCV <sub>OE</sub> /V <sub>re</sub>	<sub>f</sub> Temperature coefficient of $V_{OE}/V_{I}$	ef	≤±0.2	mV/K
TCG	Temperature coefficient of G		≤±0.05 % of	reading/K
$V_{\text{OE}}$	Electrical offset voltage @ $I_P$ = 0	, T <sub>A</sub> = 25 °C	$V_{\rm ref} \pm 0.025$	V
$V_{\rm OM}$	Magnetic offset voltage @ $I_P$ = 0			
	after an overload of $I_{\scriptscriptstyle{\mathrm{PM}}}$	HAIS 50-P/TP	<±0.5	$\%$ of $I_{\scriptscriptstyle{PN}}$
		HAIS 100-P/TP400-I	P<±0.4	$\%$ of $I_{\scriptscriptstyle{PN}}$
$t_{\rm ra}$	Reaction time to 10 % of $I_{PN}$ step	)	<3	μs
$t_{r}$	Step response time to 90 % of $I_{\rm p}$	<5	μs	
di/dt	di/dt accurately followed		>100	A/µs
$V_{no}$	Output voltage noise (DC 10	kHz)	<15	mVpp
	(DC 1 I	MHz)	<40	mVpp
BW	Frequency bandwidth (-3 dB) 5)		DC 50	kHz

Notes:

- 1) -TP version is equipped with a primary bus bar; Temperature of primary bus bar should not exceed 100 °C
- $^{2)}$  It is possible to overdrive  $V_{\rm ref}$  with an external reference voltage between 1.5 V - 2.8 V providing its ability to sink or source approximately 5 mA
- 3) Maximum supply voltage (not operating) <6.5 V
- 4) Excluding offset and magnetic offset voltage
- <sup>5)</sup> Small signal only to avoid excessive heatings of the magnetic core.

50 .. 400 A 50 .. 150 A





#### **Features**

- · Hall effect measuring principle
- Galvanic separation between primary and secondary circuit
- Insulation test voltage 2500 V
- Low power consumption
- Single power supply +5 V
- · Fixed offset & sensitivity
- Insulating plastic case recognized according to UL 94-V0.

#### **Advantages**

- · Small size and space saving
- · Only one design for wide current ratings range
- · High immunity to external interference
- V<sub>ref</sub> IN/OUT.

#### **Applications**

- · AC variable speed drives and servo motor drives
- Static converters for DC motor drives
- Battery supplied applications
- Uninterruptible Power Supplies (UPS)
- Switched Mode Power Supplies (SMPS)
- · Power supplies for welding applications.

#### **Application domain**

Industrial.

74.83.25.000.0, 74.83.34.000.0, 74.83.39.000.0, 74.83.44.000.0, 74.83.48.000.0, 74.70.25.000.0, 74.70.34.000.0, 74.70.39.000.0



#### Current Transducer HAIS 50 .. 400-P and HAIS 50 .. 150-TP

Ge	neral data			
T <sub>A</sub> T <sub>S</sub> m	Ambient operating temperature Ambient storage temperature Mass (in brackets: TP version) Standard	-40 +85 -40 +85 20 (30) EN 50178: 1997	°C °C g	
Insulation coordination				
U <sub>d</sub> U <sub>e</sub>	Rms voltage for AC insulation test, 50 Hz, 1 min Partial discharge extinction rms voltage @ 10 pC	2.5	kV	
C	HAIS 50 400-P	>1	kV	
	HAIS 50 150-TP	>1.4	kV	
$\hat{U}_{W}$	Impulse withstand voltage 1.2/50 μs	8 Min	kV	
$d_{Cp}$	Creepage distance	>8	mm	
d <sub>CI</sub>	Clearance distance	>8	mm	
CTI	Comparative Tracking Index (group I)	>600		

### **Applications examples**

According to EN 50178 and IEC 61010-1 standards and following conditions:

- Over voltage category OV 3
- Pollution degree PD2
- Non-uniform field

	EN 50178	IEC 61010-1
$d_{\text{Cp}}, d_{\text{CI}}, \hat{U}_{\text{W}}$	Rated insulation voltage	Nominal voltage
Basic insulation	1000 V	1000 V
Reinforced insulation	600 V	300 V

#### **Safety**

This transducer must be used in limited-energy secondary circuits according to IEC 61010-1.

This transducer must be used in electric/electronic equipment with respect to applicable standards and safety requirements in accordance with the manufacturer's operating instructions.

Caution, risk of electrical shock

When operating the transducer, certain parts of the module can carry hazardous voltage (eg. primary busbar, power supply). Ignoring this warning can lead to injury and/or cause serious damage.

This transducer is a build-in device, whose conducting parts must be inaccessible after installation. A protective housing or additional shield could be used. Main supply must be able to be disconnected.



#### Dimensions HAIS 50 .. 400-P and HAIS 50 .. 150-TP (in mm)

